

MMBT3906SL PNP Epitaxial Silicon Transistor

Features

- General purpose amplifier transistor.
- Ultra small surface mount package for all types(max 0.43mm tall)
- Suitable for general switching & amplification
- Well suited for portable application
- As complementary type, NPN MMBT3904SL is recommended.
- Pb free

Absolute Maximum Ratings T_a = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	200	mA
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 ~ 150	°C

I nese ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics* Ta=25°C unless otherwise noted

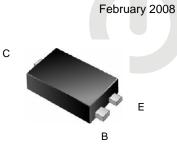
Symbol	Parameter	Max	Unit
P _C Co	ollector Power Dissipation, by $R_{\theta JA}$	227	mW
R _{0JA} The	nermal Resistance, Junction to Ambient	550	°C/W

Minimum land pad.

Electrical Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-40		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -1 {\rm mA}, I_{\rm B} = 0$	40		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$	-5		V
ICEX	Collector Cut-off Current	$V_{CE} = -30V, V_{EB(OFF)} = -0.3V$		-50	nA
h _{FE}	DC Current Gain	$V_{CE} = 1V, I_{C} = -0.1mA$ $V_{CE} = 1V, I_{C} = -1mA$	60 80		
		$V_{CE} = 1V, I_C = -10mA$ $V_{CE} = 1V, I_C = -50mA$ $V_{CE} = 1V, I_C = -100mA$	100 60 30	300	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$V_{CE} = -10$, $V_{CE} = -100$ MA $I_{C} = -10$ MA, $I_{B} = -1$ MA $I_{C} = -50$ MA, $I_{B} = -5$ MA		-0.25 -0.4	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_{C} = -10mA, I_{B} = -1mA$ $I_{C} = -50mA, I_{B} = -5mA$	-0.65	-0.85 -0.95	V V
f _T	Current Gain Bandwidth Product	$V_{CE} = -20V, I_{C} = -10mA, f = 100MHz$	250		MHz
C _{ob}	Output Capacitance	$V_{CB} = -5V, I_E = 0, f = 1MHz$		7.0	pF
C _{ib}	Input Capacitance	$V_{EB} = -0.5V, I_{C} = 0, f = 1MHz$		15	pF
t _d	Delay Time	$V_{CC} = -3V, I_{C} = -10mA$		35	ns
t _r	Rise Time	I _{B1} =- I _{B2} = -1mA		35	ns
t _s	Storage Time	1		225	ns
t _f	Fall Time	1		75	ns

* DC Item are tested by Pulse Test : Pulse Width≤300us, Duty Cycle≤2%



SOT-923F Marking : AB

Typical Performance Characteristics

Figure 1. DC Current Gain

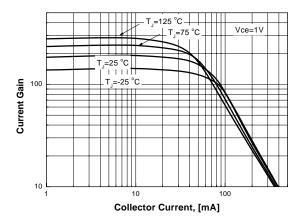
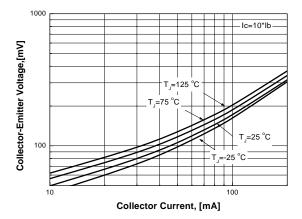
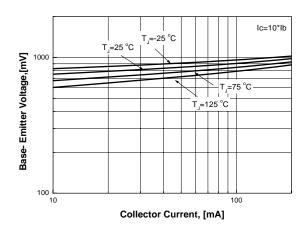
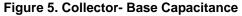


Figure 2. Collector-Emitter Saturation Voltage









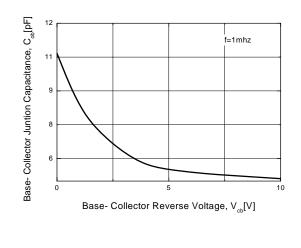
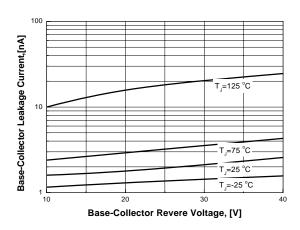
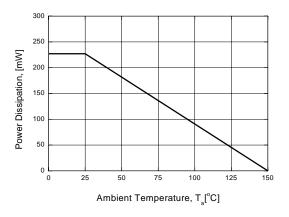
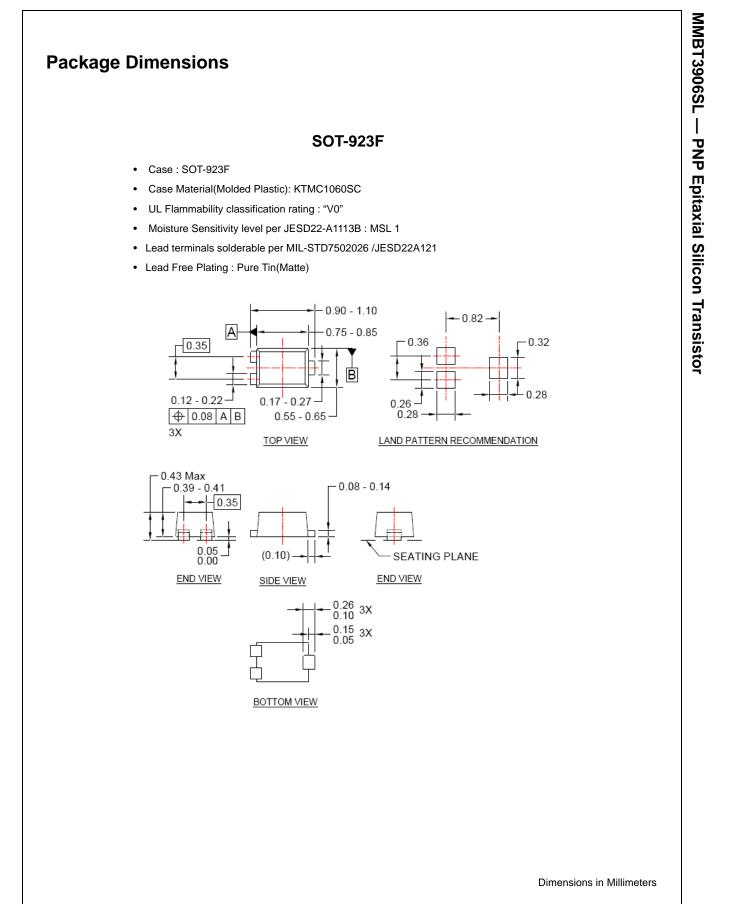


Figure 4. Collector- Base Leakage Current











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